

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S7	4	((("6475905") or ("6066569"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/06/25 03:01
S8	883	(257/635 or 257/637).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/06/25 03:07
S10	675	(257/640 or 257/643).ccls. and @ad<"20030711"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/06/25 03:09
S9	785	(257/635 or 257/637).ccls. and @ad<"20030711"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/06/25 03:09
S12	678	(257/758).ccls. and @ad<"20030711" and (barrier with (dielectric or insulat\$4 or ILD or IMD))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/06/25 03:10
S11	3050	(257/758).ccls. and @ad<"20030711"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/06/25 03:10
S13	240	(257/759.ccls. or 257/760.ccls.) and (polyimide or polysilsesquioxane or polysilsequioxane) and (SiN or nitride) and (oxide or SiO)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/25 03:11
S14	206	(257/759.ccls. or 257/760.ccls.) and (polyimide or polysilsesquioxane or polysilsequioxane) and (SiN or nitride) and (oxide or SiO) and @ad<"20030711"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/25 03:12
S16	12858	semiconductor and (polyimide or polysilsesquioxane or polysilsequioxane) and (SiN or nitride) and (oxide or SiO) and @ad<"20030711"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/25 03:20

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S15	110	(257/773).cccls. and (polyimide or polysilsequioxane or polysilsequioxane) and (SiN or nitride) and (oxide or SiO) and @ad<"20030711"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/25 03:20
S18	1740	semiconductor and (polyimide) and (barrier with (SiN or nitride)) and (oxide or SiO) and @ad<"20030711"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/25 03:21
S17	12833	semiconductor and (polyimide) and (SiN or nitride) and (oxide or SiO) and @ad<"20030711"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/25 03:21
S19	1023	semiconductor and ((polyimide) with (ILD or IMD or dielectric or insulat\$5)) and (barrier with (SiN or nitride)) and (oxide or SiO) and @ad<"20030711"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/25 03:24
L1	28	semiconductor and ((polyimide) with (ILD or IMD or dielectric or insulat\$5)) and (barrier with (SiN or nitride)) and (oxide or SiO) and @ad<"20030711" and (plug or conductor or via or contact) with (polysilicon and copper and tungsten)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/25 17:32
L2	5	semiconductor and ((polyimide) with (ILD or IMD or dielectric or insulat\$5)) and (barrier with (SiN or nitride)) and (oxide or SiO) and @ad<"20030711" and (plug or conductor or via or contact) with (polysilicon and copper and tungsten) and (bit adj line or bitline with contact) and (memory or dram)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/25 17:33